

INTEGRATED PHOTO FLASH CHARGER AND IGBT DRIVER

FEATURES

- Highly Integrated Solution to Reduce Components
- Integrated Voltage Reference
- Integrated 50-V Power Switch,
- Integrated IGBT Driver
- High Efficiency
- Programmable Peak Current, 0.9 A ~ 1.8 A
- Input Battery Voltage of 1.6 V to 12 V
- Optimized Control Loop for Fast Charge Time
- Output Voltage Feedback From Primary Side
- 16-Pin QFN Package
- Protection
 - MAX On Time
 - MAX Off Time
 - Overcurrent Shutdown to Monitor V_{DS} at the SW pin (OV_{DS})
 - Thermal Disable

APPLICATIONS

- Digital Still Cameras
- Optical Film Cameras
- Mobile Phones With Camera
- PDAs With Camera

DESCRIPTION

This device offers a complete solution for charging a photo flash capacitor from battery input, and subsequently discharging the capacitor to a xenon flash tube. The device has an integrated voltage reference, power switch, IGBT driver, and control logic blocks for charging applications and driving IGBT applications. Compared with discrete solutions, this device reduces the component count, shrinks the solution size, and eases designs for xenon tube applications. Additional advantages are a fast charging time and high efficiency from an optimized PWM control algorithm.

Other provisions of the device includes sensing the output voltage from the primary side, programmable peak current, thermal shutdown, an output pin for charge completion, and input pins for charge enable and flash enable.

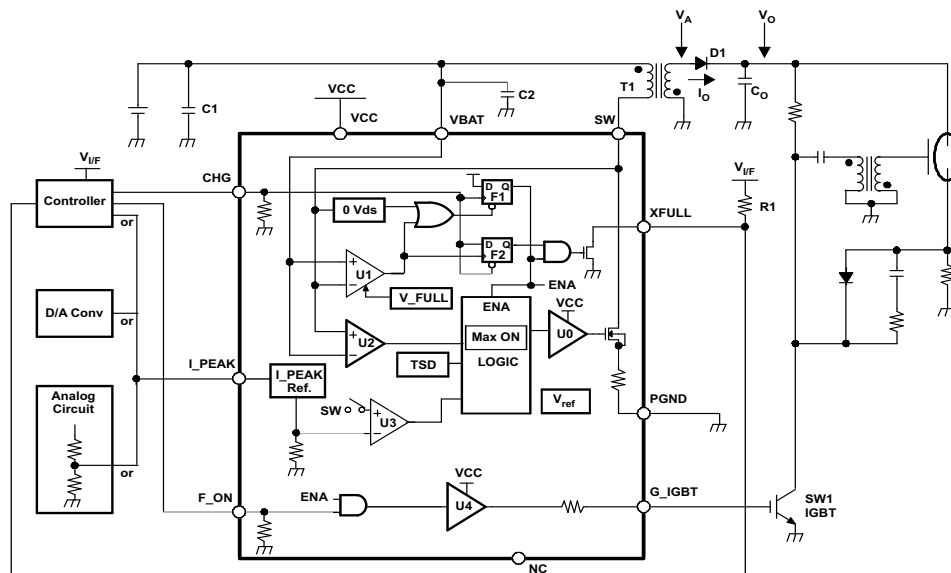


Figure 1. Typical Application Circuit

TPS65560

SLVS608–JANUARY 2006



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION

T_A	PACKAGE MARKING	PACKAGE ⁽¹⁾	PART NUMBER
-35°C to 85°C	BPR	16-pin QFN	TPS65560RGT

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

			UNIT
V_{SS}	Supply voltage	VCC	-0.6 V to 6 V
		VBAT	-0.6 V to 13 V
$V_{(SW)}$	Switch terminal voltage		-0.6 V to 50 V
$I_{(SW)}$	Switch current between SW and PGND, ISW		3 A
V_I	Input voltage of CHG, I_PEAK, F_ON		-0.3 V to V_{CC}
T_{stg}	Storage temperature		-40°C to 150°C
T_J	Maximum junction temperature		125°C
	ESD rating	HBM (Human Body Model) JEDEC JES22-A114	1 kV

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

		MIN	NOM	MAX	UNIT
V_{SS}	Supply voltage, VCC	2.7		4	V
	Supply voltage, VBAT	1.6		12	V
$V_{(SW)}$	Switch terminal voltage,	-0.3		45	V
$I_{(SW)}$	Switch current between SW and PGND			2	A
	Operating free-air temperature range	-35		85	°C
V_{IH}	High-level digital input voltage at CHG and F_ON	2			V
V_{IL}	Low-level digital input voltage at CHG and F_ON			0.5	V

DISSIPATION RATINGS

PACKAGE	$R_{\theta JA}$ ⁽¹⁾	POWER RATING $T_A < 25^\circ\text{C}$	POWER RATING $T_A = 70^\circ\text{C}$	POWER RATING $T_A = 85^\circ\text{C}$
QFN	47.4 °C/W	2.11 W	1.16 W	844 mW

(1) The thermal resistance, $R_{\theta JA}$, is based on a soldered PowerPAD™ on a 2S2P JEDEC board using thermal vias.

ELECTRICAL CHARACTERISTICS

$T_A = 25^\circ\text{C}$, $V_{\text{BAT}} = 4.2\text{ V}$, $V_{\text{CC}} = 3\text{ V}$, $V_{(\text{SW})} = 4.2\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
$R_{(\text{ONL})}$	ON resistance of XFULL		1.5	3	$\text{k}\Omega$	
$V_{(\text{PKH})}^{(1)}$	Upper threshold voltage of I_{PEAK}	$V_{\text{CC}} = 3\text{ V}$	2.4		V	
$V_{(\text{PKL})}^{(1)}$	Lower threshold voltage of I_{PEAK}	$V_{\text{CC}} = 3\text{ V}$		0.6	V	
I_{CC1}	Supply current from VBAT	CHG = H, $V_{(\text{SW})} = 0\text{ V}$ (free run by t_{MAX})	17	50	μA	
I_{CC2}	Supply current from VCC	CHG = H, $V_{(\text{SW})} = 0\text{ V}$ (free run by t_{MAX})	1.3	3	mA	
I_{CC3}	Supply current from VCC and VBAT	CHG = L		1	μA	
$I_{\text{lk}g1}$	Leakage current of SW terminal			2	μA	
$I_{\text{lk}g2}$	Leakage current of XFULL terminal	$V_{(\text{XFULL})} = 5\text{ V}$		1	μA	
$I_{(\text{sink})}$	Sink current at I_{PEAK}	$V_{(\text{L_PEAK})} = 3\text{ V}$, CHG: High		2	μA	
		$V_{(\text{L_PEAK})} = 3\text{ V}$, CHG: Low		0.1		
$R_{(\text{ONSW})}$	SW ON resistance between SW and PGND	$I_{(\text{SW})} = 1\text{ A}$, $V_{\text{CC}} = 3\text{ V}$	0.4	0.9	Ω	
$R_{(\text{IGBT1})}$	G_IGBT pullup resistance	$V_{(\text{G_IGBT})} = 0\text{ V}$, $V_{\text{CC}} = 3\text{ V}$	8	12	19.4	Ω
$R_{(\text{IGBT2})}$	G_IGBT pulldown resistance	$V_{(\text{G_IGBT})} = 3\text{ V}$, $V_{\text{CC}} = 3\text{ V}$	36	53	70	Ω
$I_{(\text{PEAK1})}$	Upper peak of $I_{(\text{SW})}$	$V_{(\text{L_IPEAK})} = 3\text{ V}$	1.58	1.68	1.78	A
$I_{(\text{PEAK2})}$	Lower peak of $I_{(\text{SW})}$	$V_{(\text{L_IPEAK})} = 0\text{ V}$	0.7	0.8	0.9	A
$V_{(\text{FULL})}$	Charge completion detect voltage at $V_{(\text{SW})}$	$V_{\text{BAT}} = 1.6\text{ V}$, $V_{\text{CC}} = 3\text{ V}$	28	28.7	29.4	V
		$V_{\text{CC}} = 3\text{ V}$	28.6	29	29.4	
$V_{(\text{ZERO})}$	Zero current detection at $V_{(\text{SW})}$		1	20	60	mV
$T_{(\text{SD})}^{(1)}$	Thermal shutdown temperature		150	160	170	$^\circ\text{C}$
	Over V_{DS} detection at $V_{(\text{SW})}$		0.95	1.2	1.45	V
t_{MIN}	MAX OFF time		25	50	80	μs
t_{MAX}	MAX ON time		50	100	160	μs
$R_{(\text{INPD})}$	Pulldown resistance of CHG, F_ON	$V_{\text{CHG}} = V_{(\text{F_ON})} = 4.2\text{ V}$		100		$\text{k}\Omega$

(1) Specified by design.

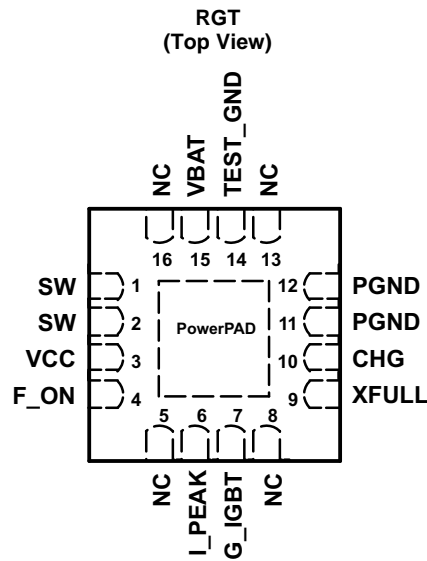
SWITCHING CHARACTERISTICS

$T_A = 25^\circ\text{C}$, $V_{\text{BAT}} = 4.2\text{ V}$, $V_{\text{CC}} = 3\text{ V}$, $V_{(\text{SW})} = 4.2\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
$t_{\text{PD}}^{(1)}$	F_ON \uparrow - G_IGBT \downarrow		50		ns	
	SW ON after $V_{(\text{SW})}$ dips from $V_{(\text{ZERO})}$		45		ns	
	SW OFF after $I_{(\text{SW})}$ exceeds $I_{(\text{PEAK})}$		270		ns	
	XFULL \downarrow after $V_{(\text{SW})}$ exceeds $V_{(\text{FULL})}$		400		ns	
	SW ON after CHG \uparrow			12		μs
	SW OFF after CHG \downarrow			20		ns

(1) Specified by design.

PIN ASSIGNMENT



NC – No internal connection

TERMINAL FUNCTIONS

PIN NUMBER	SIGNAL	I/O	DESCRIPTION
1, 2	SW	O	Primary side switch. Connect SW to the switched side of the transformer
3	VCC	I	Power supply input. Connect VCC to an input supply from 2.7 V to 4 V. Bypass VCC to GND with a 1- μ F ceramic capacitor as close as possible to the IC.
4	F_ON	I	G_IGBT control input. Drives F_ON with the flash discharge signal. A logic high on F_ON drives G_IGBT high when CHG is Low. See the <i>IGBT Driver Control</i> section for details.
5, 8, 13, 16	NC		No internal connection
6	I_PEAK	I	Primary side peak current control input. The voltage at I_PEAK sets the peak current into SW. See the <i>Programming Peak Current</i> section for details on selecting $V_{(I_PEAK)}$.
7	G_IGBT	O	IGBT gate driver output. G_IGBT swings from PGND to VCC to drive external IGBT devices.
9	XFULL	O	Charge completion indicator output. XFULL is an open-drain output that pulls low once the output is fully charged. XFULL is high impedance during charging and all fault conditions. XFULL is reseted when CHG turns Low from High. See the <i>Indicating Charging Status</i> section for details.
10	CHG	I	Charge control input. Drive CHG high to initiate charging of the output. Drive CHG low to terminate charging.
11, 12	PGND		Power ground. Connect to the ground plane.
14	TEST_GND		Used by TI, should be connected to PGND and ground plane.
15	VBAT	I	Battery voltage monitor input. Connect VBAT to an input supply from 1.6 V to 12 V. Bypass VBAT to GND with a 10- μ F ceramic capacitor (C1 in Figure 1 , as close as possible to the battery) and a 1- μ F ceramic capacitor (C2 in Figure 1 , as close as possible to the IC).

FUNCTIONAL BLOCK DIAGRAM

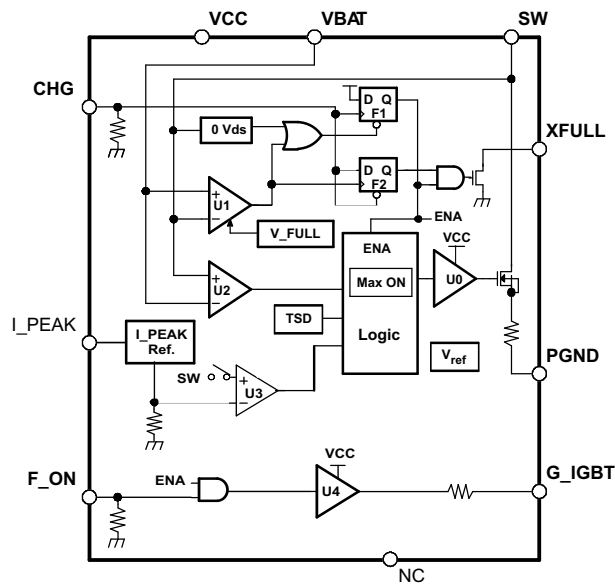


Figure 2. Functional Block Diagram

I/O Equivalent Circuits

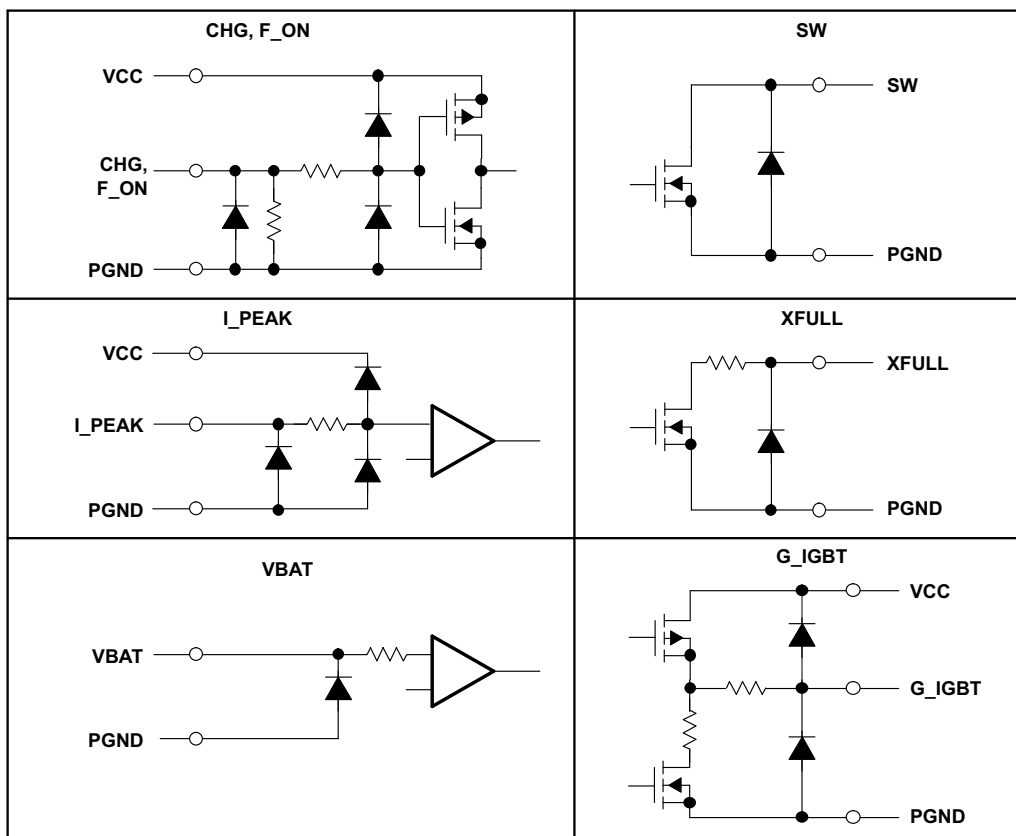


Figure 3. I/O Equivalent Circuits

PRINCIPLES OF OPERATION

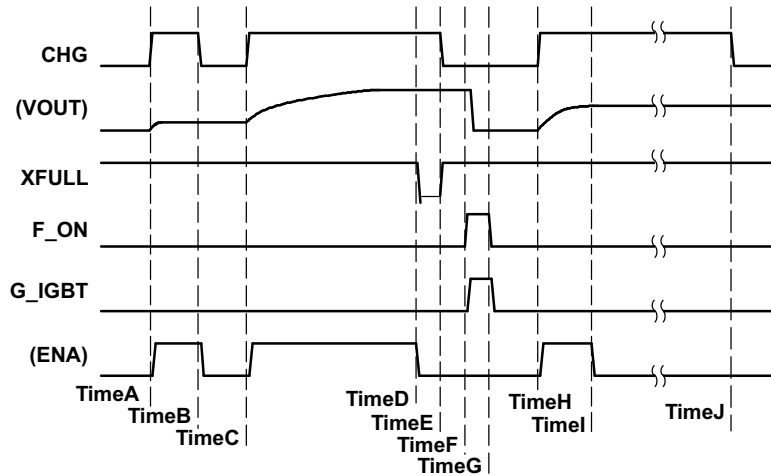


Figure 4. Whole Operation Sequence Chart

Start/Stop Charging

TPS65560 has one internal enable latch, F1, that holds the charge enable (ON/OFF status) of the device. See Figure 2.

The only way to start charging is to input CHG↑ (see time A/C/H in Figure 4). Each time CHG↑ is applied, the TPS65560 starts charging.

There are three trigger events to stop charging:

1. Forced stop by inputting CHG = L from the controller (see timeB in Figure 4).
2. Automatic stop by detecting a full charge. VOUT reaches the target value (see TimeD in Figure 4).
3. Protected stop by detecting an over current function (OV_{DS}) trigger at SW pin (see TimeI in Figure 4).

Indicating Charging Status

When the charging operation is complete, the TPS65560 drives the charge completion indicator pin, XFULL, to GND. A controller can detect the status of the device as a logic signal when connected through a pullup resistor, R1 (see Figure 1).

The XFULL output enables the controller to detect the OV_{DS} protection status. If OV_{DS} protection occurs, XFULL never goes L during CHG = H. Therefore, the controller detects OV_{DS} protection by measuring the time from CHG high to XFULL low. If the time to XFULL low is longer than the maximum designed charge time, then an OV_{DS} protection occurred.

The device starts charging at timeH, and OV_{DS} protection occurs at TimeI (see Figure 4). At TimeI, XFULL stays H. At TimeJ, the controller detects OV_{DS} protection through the expiration of a timer ends and then sets CHG to low to terminate the operation.

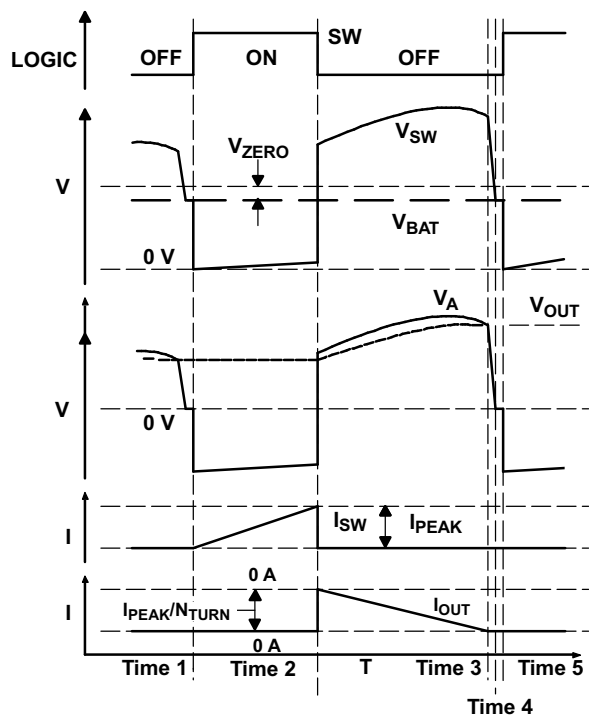


Figure 5. Timing Diagram at One Switching Cycle

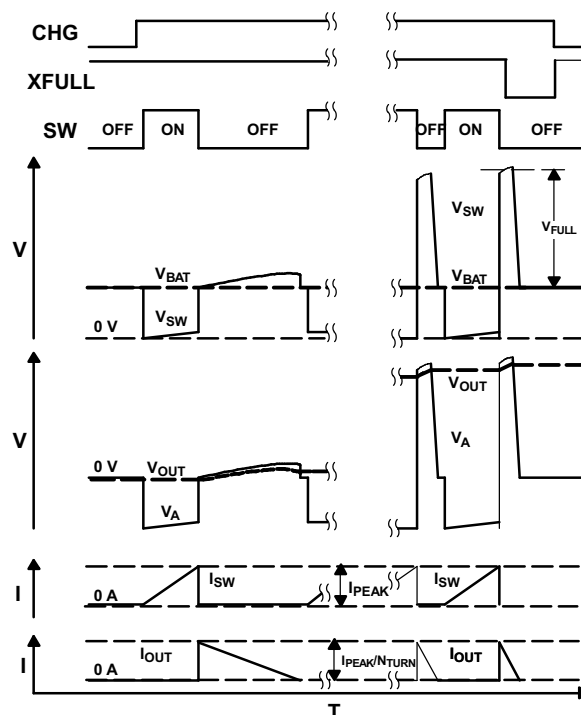


Figure 6. Timing Diagram at Beginning/Ending

Control Charging

The TPS65560 provides three comparators to control charging. Figure 2 shows the block diagram of TPS65560 and Figure 5 shows a timing diagram of one switch cycle. Note that emphasis is placed on Time1 and Time3 of the waveform in Figure 5.

While SW is ON (Time1 to Time2 in Figure 5), U3 monitors current flow through the integrated power switch from SW pin to GND. When $I_{(SW)}$ exceeds $I_{(PEAK)}$, SW turns OFF (Time2 in Figure 5).

When SW turns OFF (Time2 in Figure 5), the magnetic energy in the transformer starts discharging. Meanwhile, U2 monitors the kickback voltage at the SW terminal. As the energy is discharging, the kickback voltage is increasing according to the increase of V_O (Time2 to Time3 in Figure 5). When almost all energy is discharged, the system cannot continue rectification via the diode, and the charging current of I_O goes to zero (Times3 in Figure 5). After rectification stops, the small amount of energy left in the transformer is released via parasitic paths, and the kickback voltage reaches zero (Time3 to Time4 in Figure 5). During this period, U2 makes SW turn ON when $(V_{(SW)} - V_{BAT})$ dips from $V_{(ZERO)}$ (Time5 in Figure 5). In the actual circuit, the period between Time4 and Time5 in Figure 5 is small or does not appear dependent on the delay time of the U2 detection to SW ON.

U1 also monitors the kickback voltage. When $(V_{(SW)} - V_{BAT})$ exceeds $V_{(FULL)}$, the TPS65560 stops charging (see Figure 6).

In Figure 5 and Figure 6, ON time is always the same period in every switch cycle. The ON time is calculated by Equation 1. L and $I_{(PEAK)}$ are selected to ensure that t_{ON} does not exceed the MAX ON time (t_{MAX}).

$$t_{ON} = L \frac{I_{PEAK}}{V_{BAT}} \tag{1}$$

The *OFF* time is dependant on output voltage. As the output voltage gets higher, the *OFF* time gets shorter (see Equation 2).

$$t_{OFF} = N_{TURN} \times L \frac{I_{PEAK}}{V_{OUT}} \tag{2}$$

Programming Peak Current

The TPS65560 provides a method to program the peak primary current with a voltage applied to the I_PEAK pin. Figure 7 shows how to program I_(PEAK).

The I_PEAK input is treated as a logic input below V_(PKL) (0.6 V) and above V_(PKH) (2.4 V). Between V_(PKL) and V_(PKH), I_PEAK input is treated as an analog input. Using this characteristic, I_(PEAK) can be set by a logic signal or by an analog input.

Typical usages of this function are:

1. Setting the peak charging currents based on the battery voltage. Larger I_(PEAK) for a fully charged battery and lower I_(PEAK) for a discharged battery.
2. Reducing I_(PEAK) when powering a zooming lens motor. This avoids inadvertent shutdowns due to large current from the battery.

In Figure 1, three optional connections to I_PEAK are shown.

1. Use the controller to treat I_PEAK as the logic input pin. This option is the easiest.
2. Use a D/A converter to force I_(PEAK) to follow analog information, such as battery voltage.
3. Use an analog circuit to achieve the same results as the D/A converter.

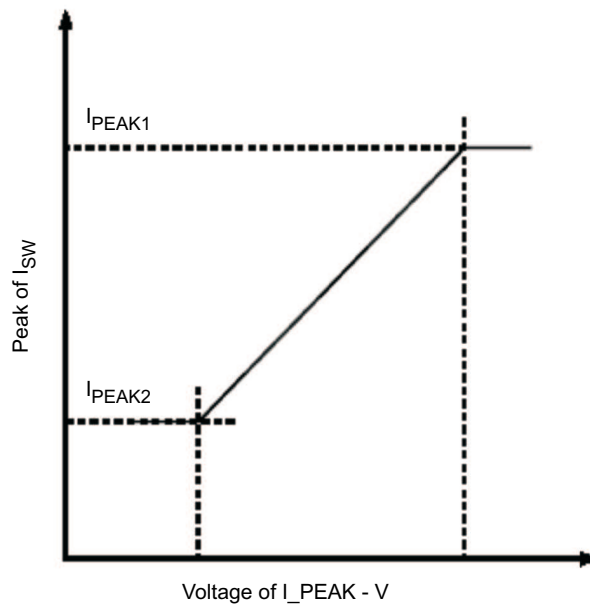


Figure 7. I_PEAK vs I_(sw)

IGBT Driver Control

The IGBT driver is provided by the TPS65560. The driver voltage depends on VCC. TPS65560 has a mask filter as shown in Figure 8. The mask does not have hysteresis; therefore, there is no wait time from CHG forcing Low after FULL CHARGE to F_ON turning High.

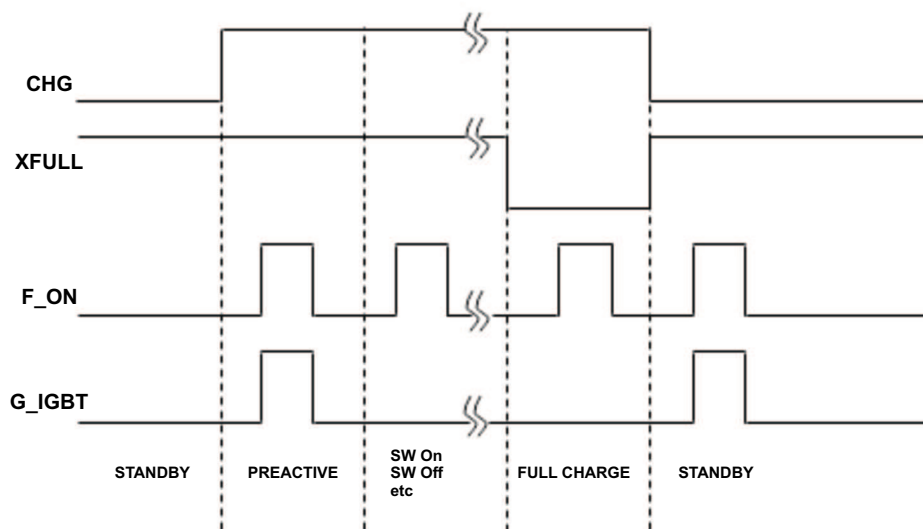


Figure 8. IGBT Timing Diagram

Protections

TPS65560 provides four protection mechanisms: max on time, max off time, thermal disable, and overcurrent shutdown.

MAX On Time

To prevent a condition such as pulling current from a poor power source (i.e., an almost empty battery), and never reaching peak current, the TPS65560 provides a maximum ON time function. If the ON time exceeds t_{MAX} , the TPS5560 is forced OFF regardless of $I_{(PEAK)}$ detection.

MAX Off Time

To prevent a condition such as never increasing the voltage at the SW pin when the internal FET is OFF, the TPS65560 provides a maximum OFF time function. If the OFF time exceeds t_{MIN} , the TPS65560 is forced ON regardless of $V_{(ZERO)}$ detection.

Thermal Disable

Once the TPS65560 die temperature reaches 160°C, all functions stop. Once the die cools below 160°C, the TPS65560 restarts charging if CHG remains high during the entire overtemperature condition.

Overcurrent Shutdown to Monitor V_{DS} at the SW Pin (OV_{DS})

The TPS65560 provides an overvoltage monitor function of the SW pin. The TPS65560 is latched off if the voltage on the SW pin is above OV_{DS} during the switch ON time (see Figure 4 and its descriptions).

This function protects against short-circuits on the primary side of the transformer. A short-circuit of the primary side shorts the battery voltage to GND. SW pin can damage the device if not protected.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS65560RGTR	ACTIVE	QFN	RGT	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR		BPR	Samples
TPS65560RGTT	ACTIVE	QFN	RGT	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR		BPR	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

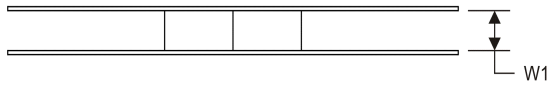
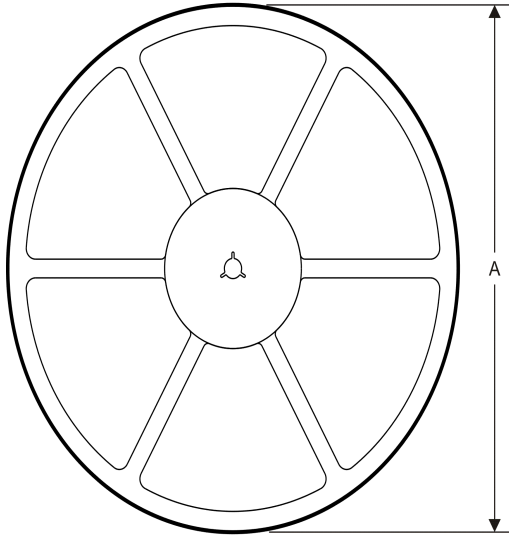
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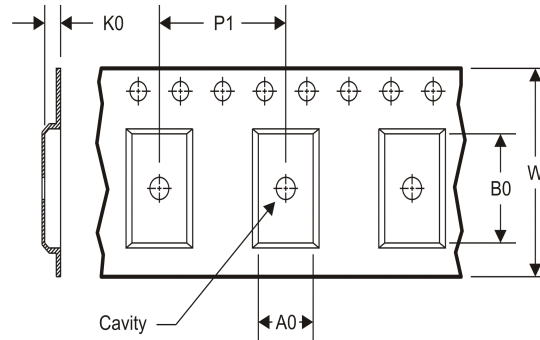
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



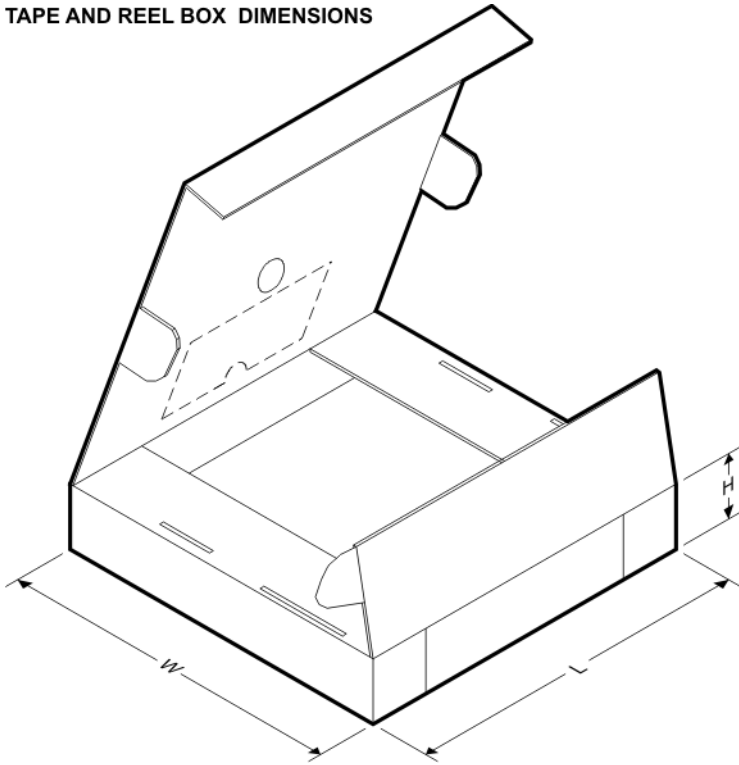
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS65560RGTR	QFN	RGT	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS65560RGTT	QFN	RGT	16	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS

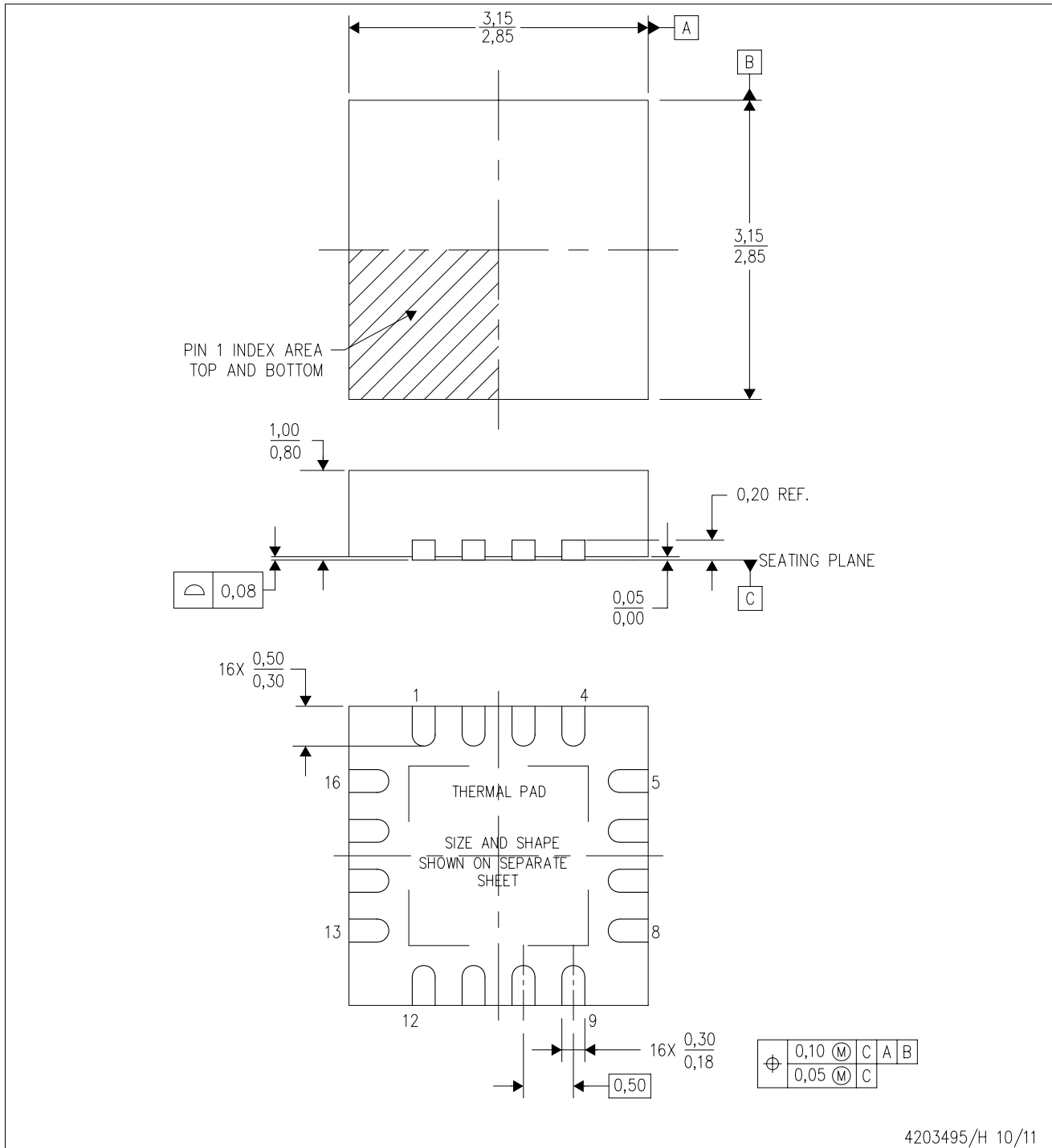


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS65560RGTR	QFN	RGT	16	3000	367.0	367.0	35.0
TPS65560RGTT	QFN	RGT	16	250	210.0	185.0	35.0

RGT (S-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



4203495/H 10/11

- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - Quad Flatpack, No-leads (QFN) package configuration.
 - The package thermal pad must be soldered to the board for thermal and mechanical performance.
 - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
 - Falls within JEDEC MO-220.

THERMAL PAD MECHANICAL DATA

RGT (S-PVQFN-N16)

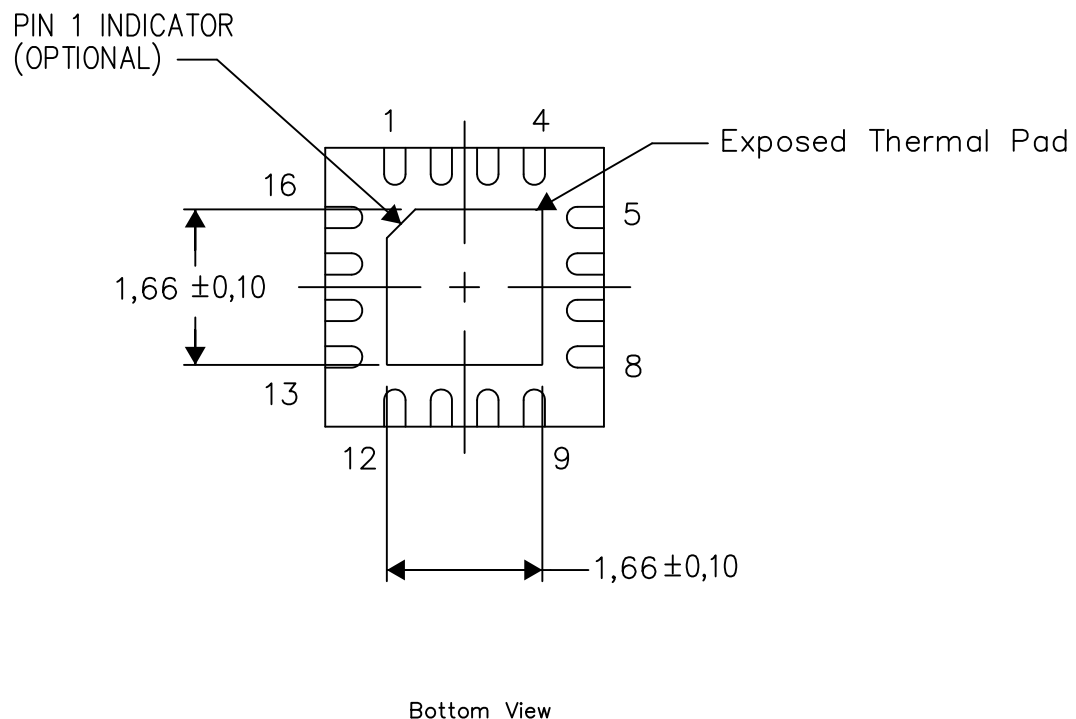
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



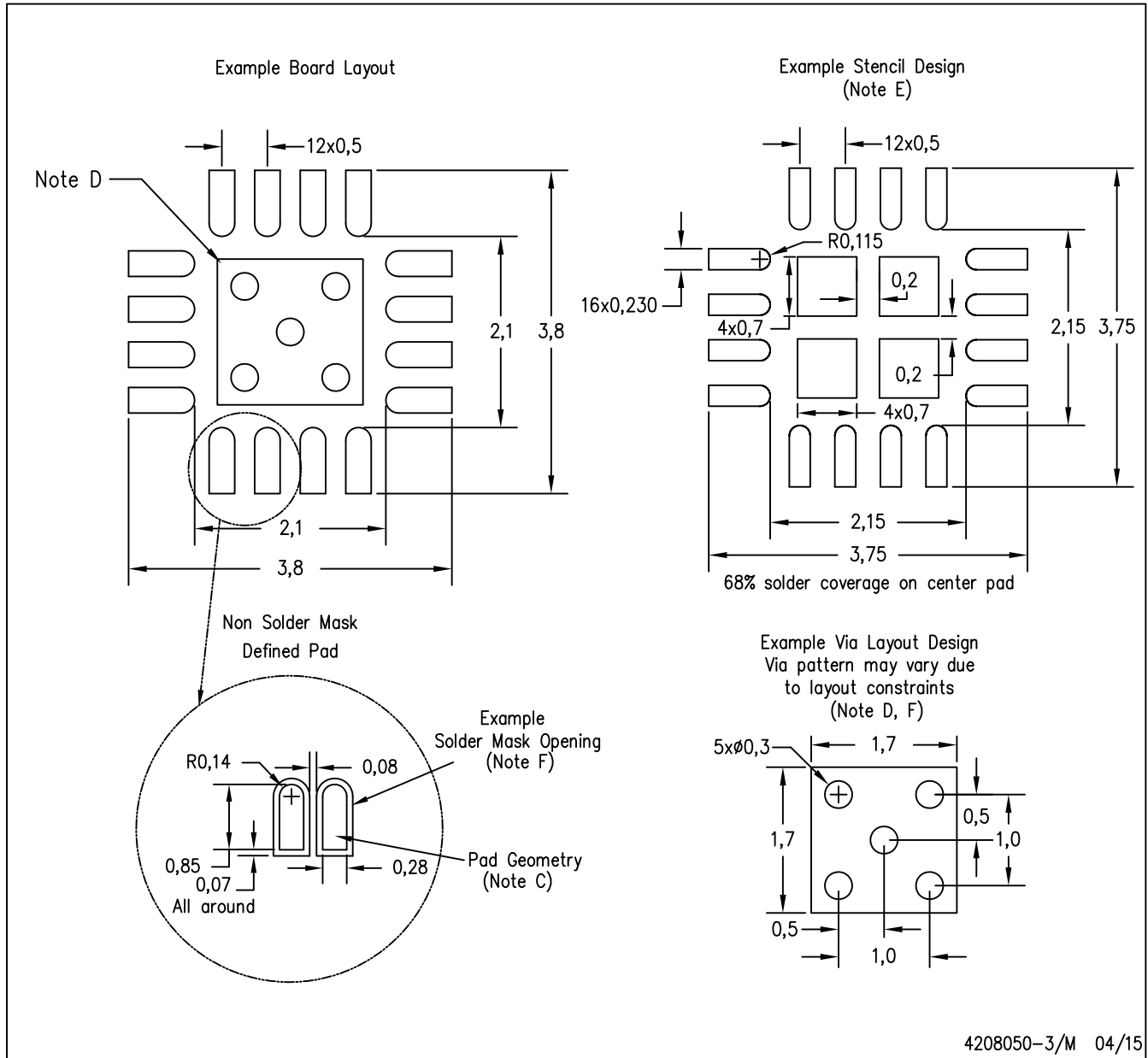
Exposed Thermal Pad Dimensions

4206349-10/Z 08/15

NOTE: All linear dimensions are in millimeters

RGT (S-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <<http://www.ti.com>>.
 - E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.